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Manufacturers of World Class Discrete Semiconductors

2N3055 NPN
MJ2955 PNP

COMPLEMENTARY SILICON
POWER TRANSISTORS

JEDEC TO-3 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3055, MJ2955 types are complementary silicon power transistors manufactured by the epitaxial base process, mounted in a hermetically sealed metal case designed for general purpose switching and amplifier applications.

MAXIMUM RATINGS (T_C=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CER}	70	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EB0}	7.0	V
Collector Current	I _C	15	A
Base Current	I _B	7.0	A
Power Dissipation	P _D	115	W
Operating and Storage Junction Temperature	T _J , T _{STG}	-65 TO +200	°C
Thermal Resistance	θ _{JC}	1.52	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{CEV}	V _{CE} =100V, V _{EB} (OFF)=1.5V		1.0	mA
I _{CEV}	V _{CE} =100V, V _{EB} (OFF)=1.5V, T _C =150°C		5.0	mA
I _{CEO}	V _{CE} =30V		0.7	mA
I _{EB0}	V _{BE} =7.0V		5.0	mA
BV _{CEO}	I _C =200mA	60		V
BV _{CER}	I _C =200mA, R _{BE} =100Ω	70		V
V _{CE} (SAT)	I _C =4.0A, I _B =400mA		1.1	V
V _{CE} (SAT)	I _C =10A, I _B =3.3A		3.0	V
V _{BE} (ON)	V _{CE} =4.0V, I _C =4.0A		1.5	V
h _{FE}	V _{CE} =4.0V, I _C =4.0A	20	70	
h _{FE}	V _{CE} =4.0V, I _C =10A	5.0	-	
h _{fe}	V _{CE} =4.0V, I _C =1.0A, f=1.0kHz	15	120	
f _T	V _{CE} =10V, I _C =0.5A, f=1.0MHz	2.5		MHz
f _{hfe}	V _{CE} =4.0V, I _C =1.0A, f=1.0kHz	10		kHz
I _s /b	V _{CE} =40V, t=1.0s	2.87		A